# DISCRETE SEMICONDUCTORS

# DATA SHEET

# BT151U series C Thyristors

**Product specification** 

August 2018



#### **Thyristors**

static switching.

## BT151U series C

#### **GENERAL DESCRIPTION**

# Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and

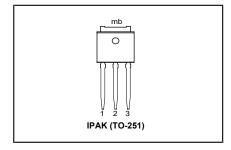
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT151U- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	500C 500 7.5 12 100	650C 650 7.5 12 100	800C 800 7.5 12 100	V A A A

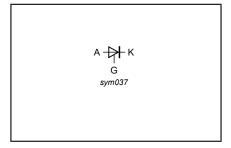
#### **PINNING - SOT533, (I-PAK)**

PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

#### **PIN CONFIGURATION**



#### SYMBOL



#### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V <sub>DRM</sub> , V <sub>RRM</sub>	Repetitive peak off-state voltages		-	<b>-500C</b> 500 <sup>1</sup>	<b>-650C</b> 650 <sup>1</sup>	<b>-800C</b> 800	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 104 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge	- -		7.5 12		A A
l <sup>2</sup> t dl <sub>T</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of	t = 10 ms t = 8.3 ms t = 10 ms l <sub>TM</sub> = 20 A; l <sub>G</sub> = 50 mA; dl <sub>G</sub> /dt = 50 mA/μs	- - -		100 110 50 50		Α Α Α²s Α/μs
I <sub>GM</sub> V <sub>RGM</sub> P <sub>GM</sub> P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>i</sub>	on-state current after triggering Peak gate current Peak reverse gate voltage Peak gate power Average gate power Storage temperature Junction temperature	over any 20 ms period	- - - -40 -		2 5 5 0.5 150 125		٥°%

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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#### THERMAL RESISTANCES

CONDITIONS	MIN.	TYP.	MAX.	UNIT
in free air	-	- 70	1.3 -	K/W K/W K/W
		-		1.3

#### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mA
l I	Latching current	$V_{\rm D}^{\rm S} = 12 \text{ V}; I_{\rm GT}^{\rm T} = 0.1 \text{ A}$	-	10	40	mA
l <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	7	20	mA
Ϋ́Τ	On-state voltage	$I_{T} = 23 \text{ A}$	-	1.44	1.75	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 A$ ; $T_j = 125 °C$	0.25	0.4	-	V
I <sub>D</sub> , I <sub>R</sub>	Off-state leakage current	$V_D = V_{DRM(max)}^{Station (max)}; V_R = V_{RRM(max)}; T_i = 125 °C$	-	0.1	0.5	mΑ

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM}$ = 67% $V_{DRM(max)}$ ; $T_j$ = 125 °C; exponential waveform Gate open circuit $R_{GK}$ = 100 Ω	50 200	130 1000	-	V/μs V/μs
t <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; \\ dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$V_D = 67\% \ V_{DRM(max)}; T_j = 125 \ ^{\circ}C; I_{TM} = 20 \ A; V_R = 25 \ V; dI_{TM}/dt = 30 \ A/\mu s; dV_D/dt = 50 \ V/\mu s; R_{GK} = 100 \ \Omega$	-	70	-	μs

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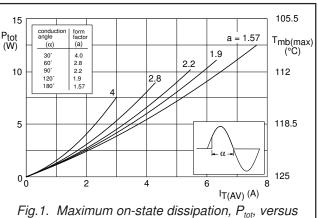


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$ .

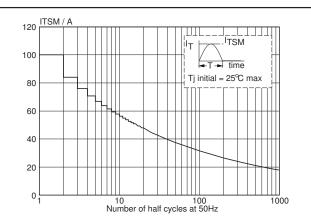


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{\text{TSM}}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

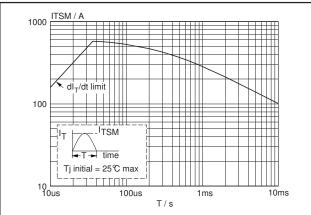


Fig.2. Maximum permissible non-repetitive peak on-state current  $l_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

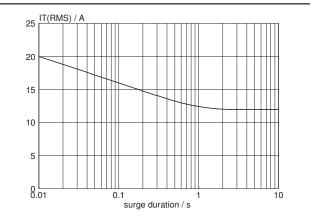


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 100$  °C.

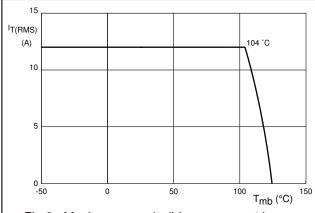
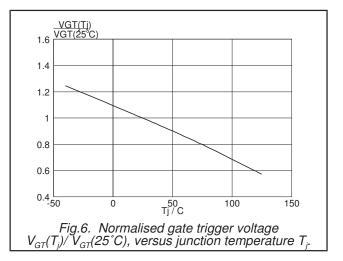
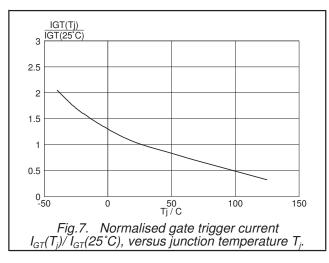
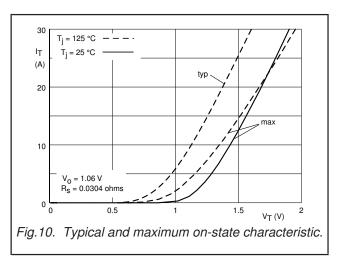


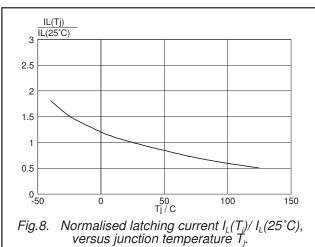
Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

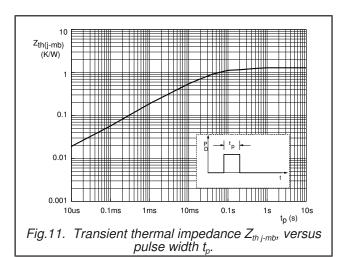


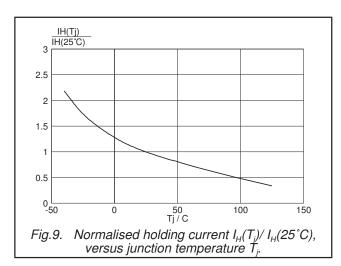
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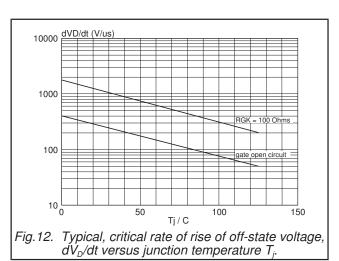












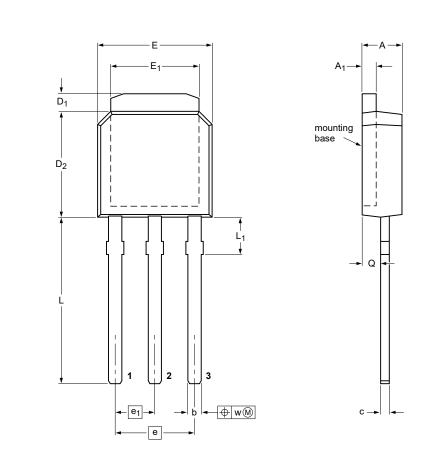
**Thyristors** 

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#### **MECHANICAL DATA**



SOT533



#### **DIMENSIONS** (mm are the original dimensions)

ı	JNIT	Α	A <sub>1</sub>	b	С	D <sub>1</sub>	D <sub>2</sub>	Е	E <sub>1</sub>	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(2)</sup> max	ď	v
	mm										2.285 BSC <sup>(1)</sup>		2.7	1.1 1.0	0.3

#### Notes

- 1. Basic spacing between centers.
- 2. Terminal dimensions are uncontrolled within zone  $L_1$ .

OUTLINI		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSIO	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT533		TO-251			<del>-05-02-11</del> 06-02-14

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#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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